



05NM65-FD

Power MOSFET

0.5A, 650V N-CHANNEL SUPER-JUNCTION MOSFET

DESCRIPTION

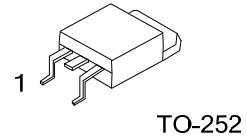
The UTC **05NM65-FD** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics.

This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

* $R_{DS(on)} < 14\Omega$ @ $V_{GS}=10V$, $I_D=0.25A$

* High breakdown voltage



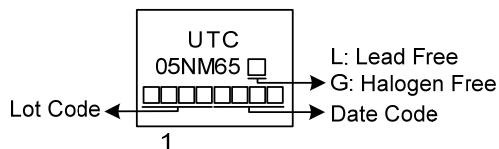
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
05NM65L-TN3-R	05NM65G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

05NM65G-TN3-R	(1)Packing Type	(1) R: Tape Reel
	(2)Package Type	(2) TN3: TO-252
	(3)Green Package	(3) G: Halogen Free and Lead Free L: Lead Free

MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DS}	650	V
Gate-Source Voltage		V_{GS}	± 30	V
Drain Current	Continuous	I_D	0.5	A
	Pulsed (Note 2)	I_{DM}	1.5	A
Peak Diode Recovery dv/dt (Note 4)		dv/dt	8	V/ns
Power Dissipation		P_D	28	W
Junction Temperature		T_J	150	$^{\circ}\text{C}$
Storage Temperature Range		T_{STG}	$-55 \sim +150$	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

4. $I_{SD} \leq 0.5\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J=25^{\circ}\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	110	$^{\circ}\text{C}/\text{W}$
Junction to Case	θ_{JC}	4.46	$^{\circ}\text{C}/\text{W}$

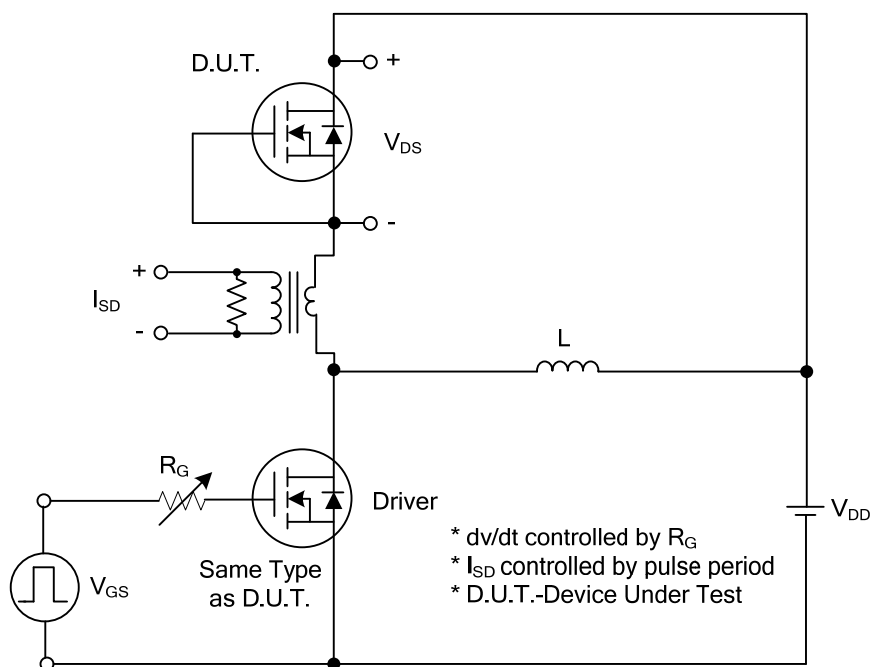
■ ELECTRICAL CHARACTERISTICS ($T_J=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	650			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =650V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =0.25A			14	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		36		pF
Output Capacitance		C _{OSS}			30		pF
Reverse Transfer Capacitance		C _{RSS}			4		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =300V, V _{GS} =10V, I _D =0.5A, I _G =1mA (Note 1, 2)		6.8		nC
Gate to Source Charge		Q _{GS}			2.2		nC
Gate to Drain Charge		Q _{GD}			1.74		nC
Turn-ON Delay Time (Note 1)		t _{D(ON)}	V _{DS} =300V, V _{GS} =10V, I _D =0.5A, R _G =25Ω (Note 1, 2)		1.8		ns
Rise Time		t _R			10		ns
Turn-OFF Delay Time		t _{D(OFF)}			7.6		ns
Fall-Time		t _F			68		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				0.5	A
Maximum Body-Diode Pulsed Current		I _{SM}				1.5	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =0.5A, V _{GS} =0V			1.4	V
Reverse Recovery Time (Note 1)		t _{rr}	V _{GS} =0V, I _S =1.0A		88		ns
Reverse Recovery Charge		Q _{rr}	dI _F /dt=100A/μs (Note1)		167		μC

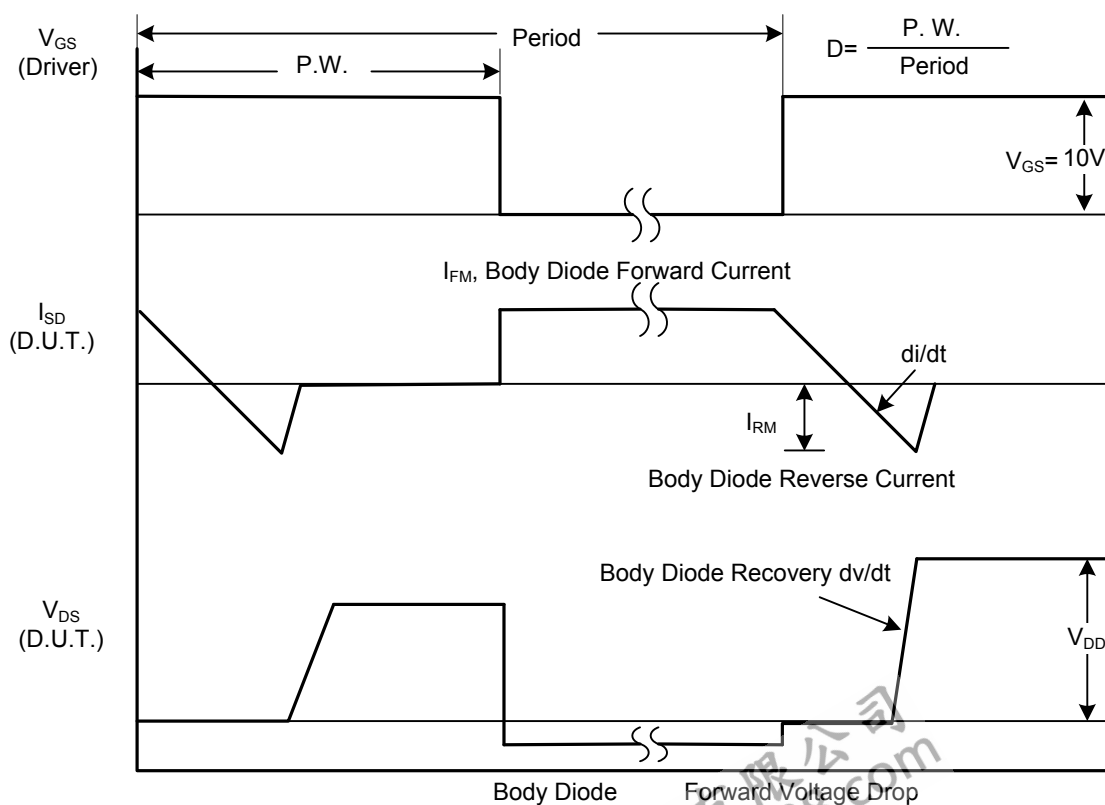
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

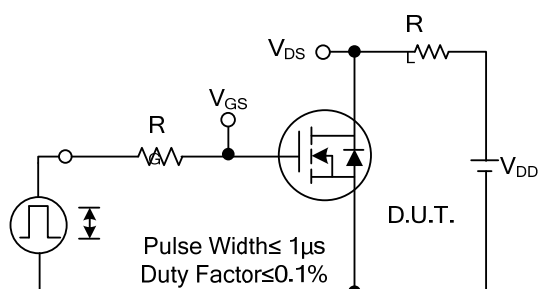


Peak Diode Recovery dv/dt Test Circuit

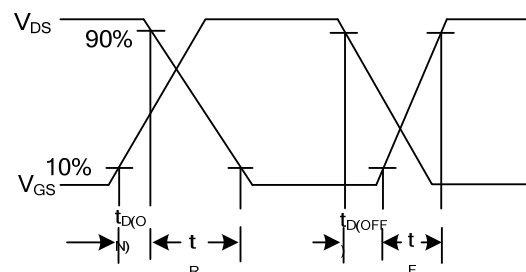


Peak Diode Recovery dv/dt Waveforms

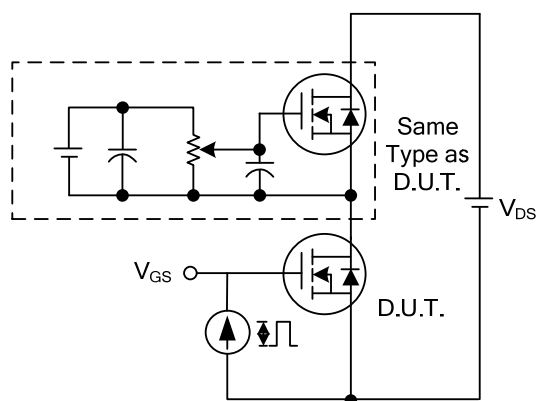
TEST CIRCUITS AND WAVEFORMS



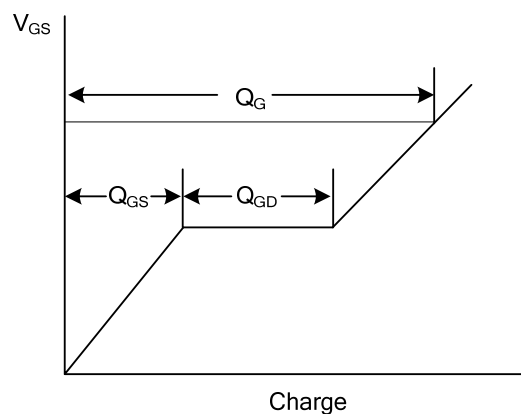
Switching Test Circuit



Switching Waveforms

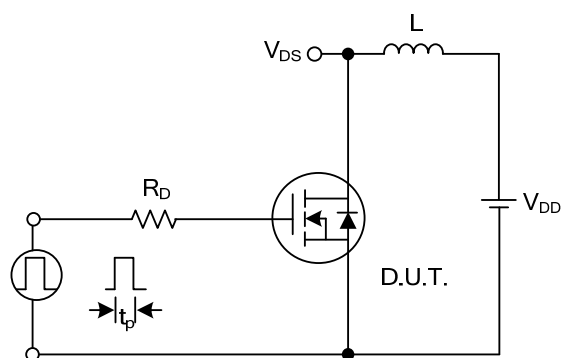


Gate Charge Test Circuit

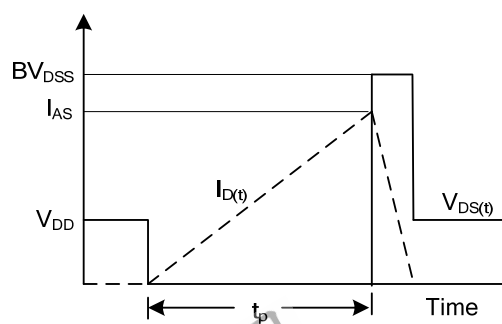


Charge

Gate Charge Waveform

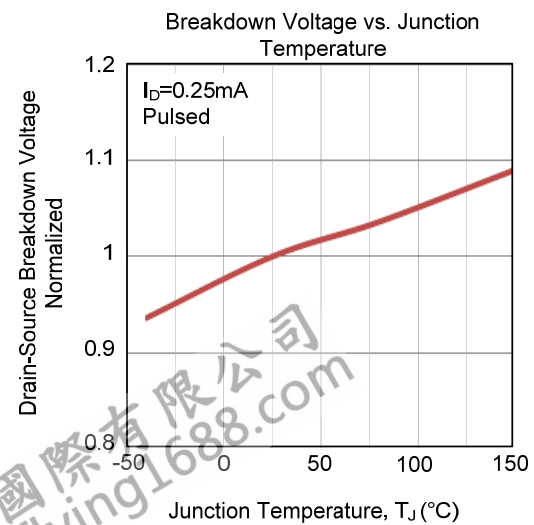
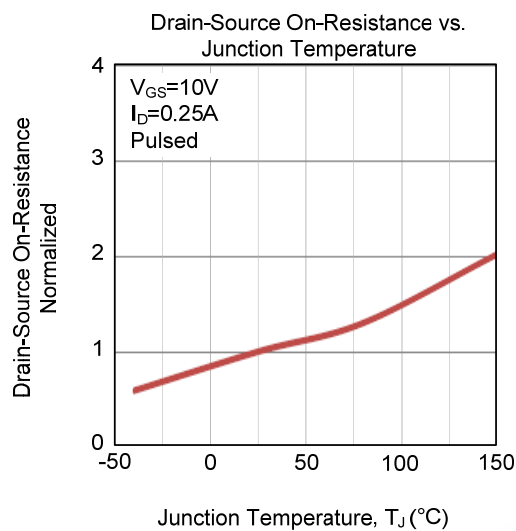
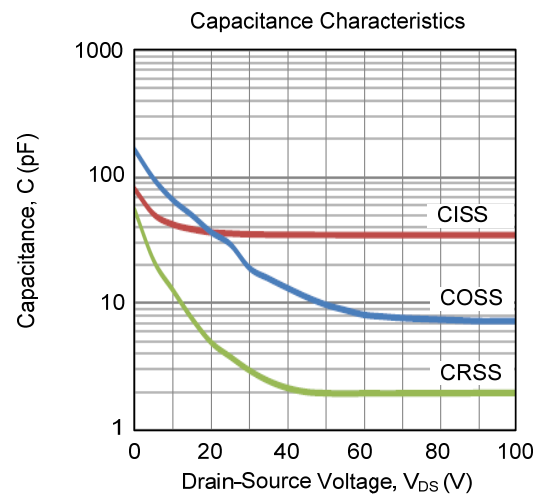
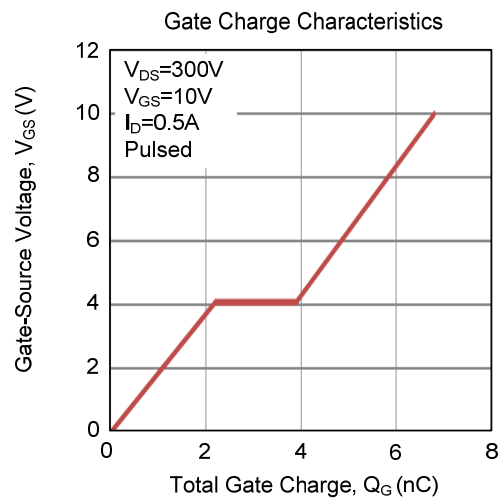
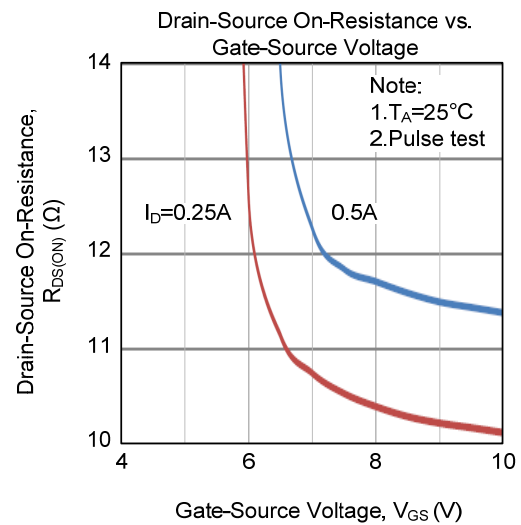
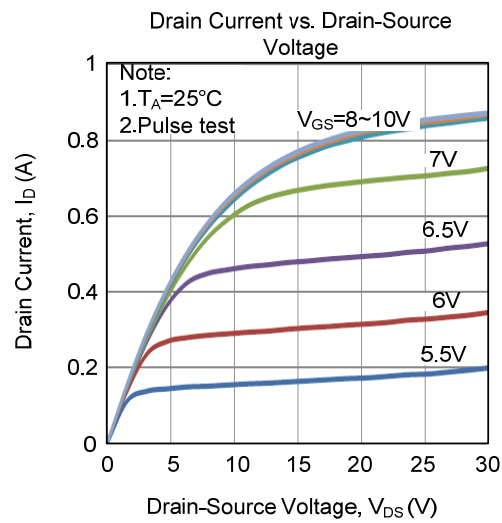


Unclamped Inductive Switching Test Circuit

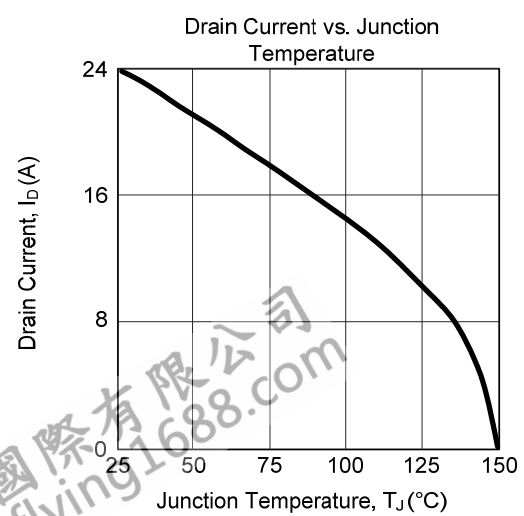
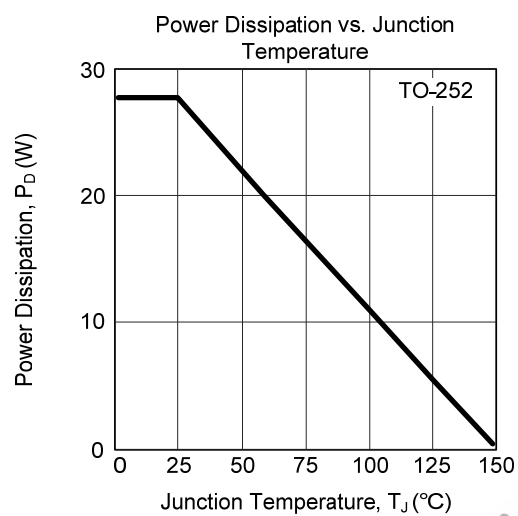
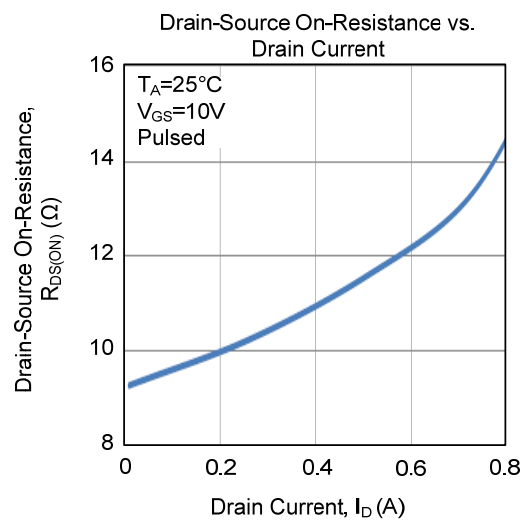
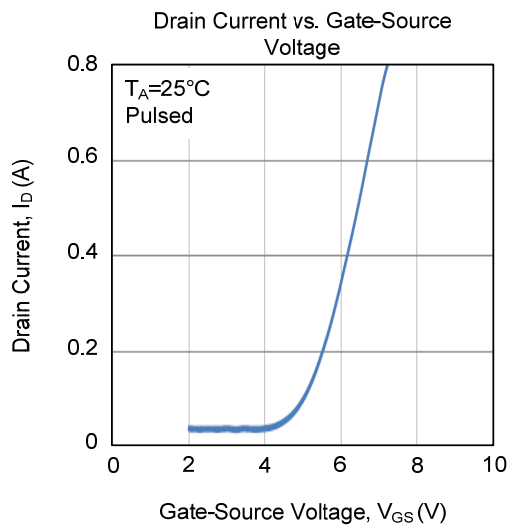
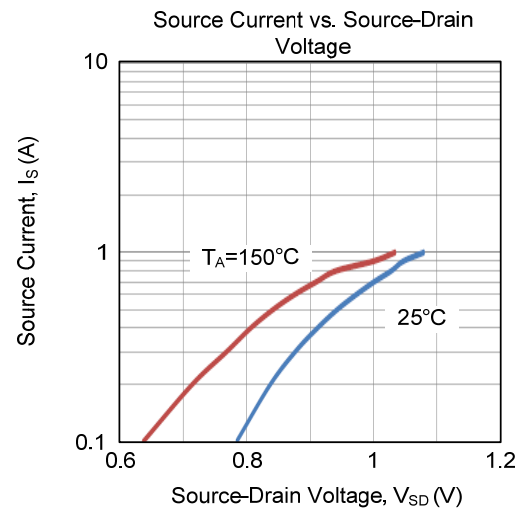
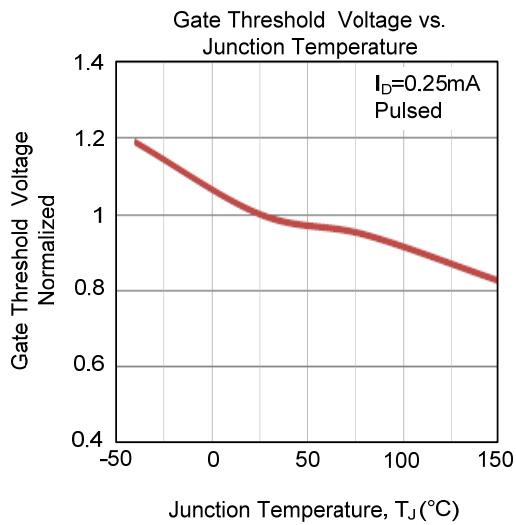


Unclamped Inductive Switching Waveforms

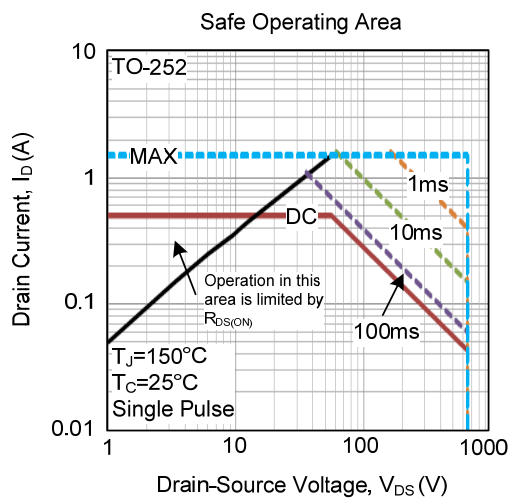
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



TYPICAL CHARACTERISTICS (Cont.)



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